

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

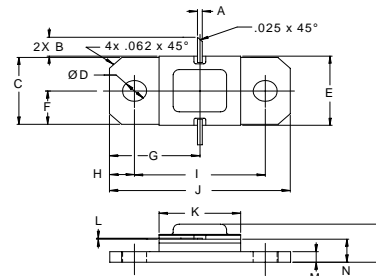
The **ASI AJT085** is Designed for 960 – 1215 MHz, JTIDS Applications.

FEATURES:

- Internal Input/Output Matching Network
- $P_G = 7.5$ dB at 85 W/ 1215 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CC}	40 V
P_{DISS}	300 W @ $T_C \leq 100$ °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.75 °C/W

PACKAGE STYLE .400 2NL FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F	.193 / 4.90	
G	.450 / 11.43	
H	.125 / 3.18	
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10547
CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25$ mA	55			V
BV_{CER}	$I_C = 25$ mA $R_{BE} = 10$ Ω	55			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CES}	$V_{CE} = 35$ V			20	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 2.0$ A	20		200	---
P_G	$V_{CC} = 50$ V $P_{OUT} = 85$ W $f = 960 - 1215$ MHz	7.5			dB
η_C		40			%